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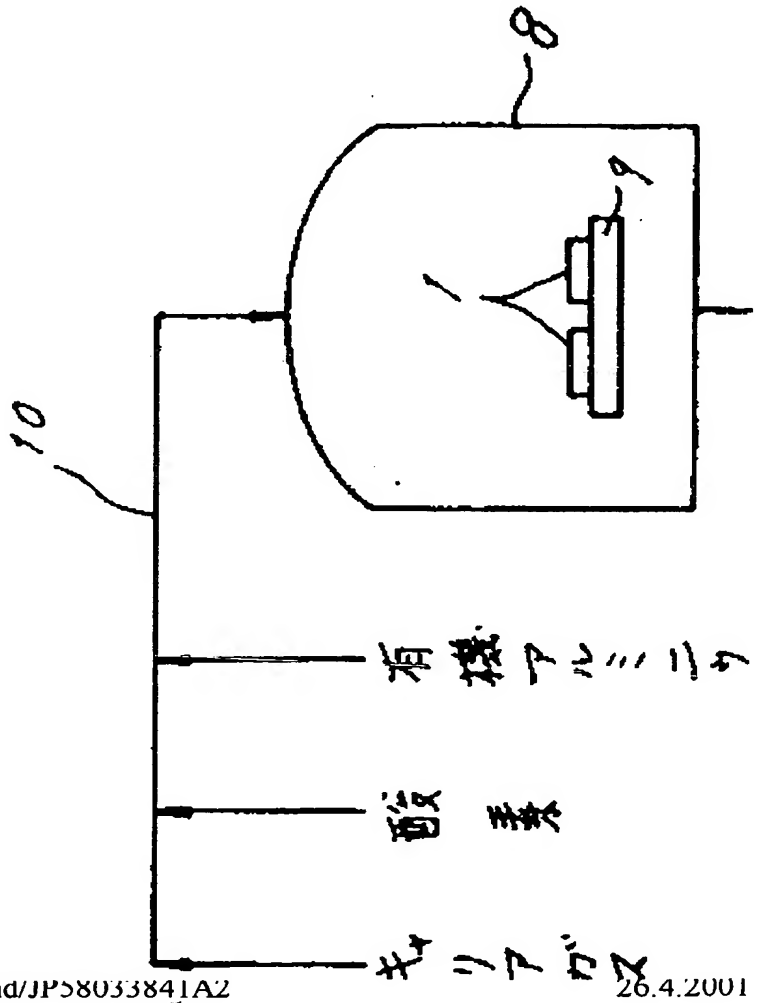
(54) SEMICONDUCTOR DEVICE

(57) Abstract:

PURPOSE: To simply and clearly form an oxidized aluminum film by forming the film by a chemical vapor growth using organic aluminum compound and oxidative gas.

CONSTITUTION: A semiconductor substrate 1 is set on a susceptor 9 in a reaction container 8. Reaction gas and carrier gas are supplied through a conduit 10 while heating the interior of the container 8 to the prescribed reaction temperature, and waste gas is exhausted from a conduit 11. The reaction gas to be used includes organic aluminum compound to become an aluminum supply source and oxidative gas such as oxygen or the like, and the carrier gas includes nitrogen or argon gas. An Al2O3 film can be readily formed at a low temperature in the desired thickness merely by controlling by this reaction device the reaction conditions such as reaction gas flow rate and the like.



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TI - SEMICONDUCTOR DEVICE
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